

**IN THE SPECIFICATION**

**Please amend the paragraph beginning at page 12 bridging page 13, beginning at line 9 of page 13, as follows:**

Figs. 2 to 8 are characteristic diagrams of the spectroscopic sensor shown in Fig. 1. Fig. 2 shows the case where  $V_g$  is -1 V, Fig. 3 shows the case where  $V_g$  is 0 V, Fig. 4 shows the case where  $V_g$  is 1 V, Fig. 5 shows the case where  $V_g$  is 2 V, Fig. 6 shows the case where  $V_g$  is 3 V, Fig. 7 shows the case where  $V_g$  is 4 V, and Fig. 8 shows the case where  $V_g$  is 5 V. Here,  $V_g$  represents a gate voltage (electric potential of the gate electrode 8). In each figure, the value 0.0 in the Z coordinate axis represents the surface of the p-type diffusion layer, the actual line represents a depth (position) W from the surface of the p-type diffusion layer in which electrons are captured, B represents a p-well part, and C represents a pn junction part with the substrate (these are representatively shown in Fig. 2 but are the same in Figs. 3 to [8] 10).